SILICON (Si) POWER MOSFET A CEM9407A



CEM9407A

-60V ▲ 100mΩ ▲ -3.7A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type P-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

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FREE

RoHS



Parameter ($T_A = 25^{\circ}C$, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-60V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current	I _D	-3.7A
Pulsed Drain Current Note 1	I _{DM}	-14.8A
Maximum Power Dissipation	PD	2.5W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{th_ja}	50°C/W

APPLICATIONS

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
			4	Y

PIN DESCRIPTION

Circuit Diagram	Outline - Top View	Pin No.	Description
D (5,6,7,8)	8765 AAA	1 2	Source Source
G (4)		3	Source Gate
	0	5	Drain Drain
 S (1,2,3)		7 8	Drain Drain

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ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250 \mu A$	BV _{DSS}	-60			V
Zero Gate Voltage Drain Current	V_{DS} = -48V, V_{GS} = 0V	I _{DSS}			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	V _{GS(th)}	-1		-3	V
Static Drain-Source On-Resistance	V _{GS} = -10V, I _D = -3.7A	R _{DS(ON)}		100	125	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V$, $I_{D} = -3.1A$	R _{DS(ON)}		130	165	mΩ
Forward Transconductance	V _{DS} = -5V, I _D = -3.1A	g FS		7		S
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -30V, V_{GS} = 0V, f = 1MHz$	C _{ISS}		615		рF
Output Capacitance	V_{DS} = -30V, V_{GS} = 0V, f = 1MHz	Coss		140		рF
Reverse Transfer Capacitance	V_{DS} = -30V, V_{GS} = 0V, f = 1MHz	C _{RSS}		45		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = -30V, V_{GS} = -10V, I_{D} = -1A, $R_{\text{G(ext)}}$ = 6 Ω	t _{D(ON)}		11	22	ns
Turn-On Rise Time	V_{DD} = -30V, V_{GS} = -10V, I_{D} = -1A, $R_{\text{G(ext)}}$ = 6 Ω	t _R		4.5	9	ns
Turn-Off Delay Time	V_{DD} = -30V, V_{GS} = -10V, I_{D} = -1A, $R_{\text{G(ext)}}$ = 6 Ω	t _{D(OFF)}		50	100	ns
Turn-Off Fall Time	V_{DD} = -30V, V_{GS} = -10V, I_{D} = -1A, $R_{\text{G(ext)}}$ = 6Ω	t _F		15	30	ns
Total Gate Charge	V_{DS} = -30V, V_{GS} = -10V, I_{D} = -3.7A	Q_{G}		17	22	nC
Gate Source Charge	V_{DS} = -30V, V_{GS} = -10V, I_{D} = -3.7A	Q _{GS}		2		nC
Gate Drain Charge	V_{DS} = -30V, V_{GS} = -10V, I_{D} = -3.7A	\mathbf{Q}_{GD}		4		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		ls			-1.3	А
Drain-Source Diode Forward Voltage Note 3	V _{GS} = 0V, I _S = -1.3A	V_{SD}			-1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, $t \le 10$ sec
- 3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4: Guaranteed by design, not subject to production testing.

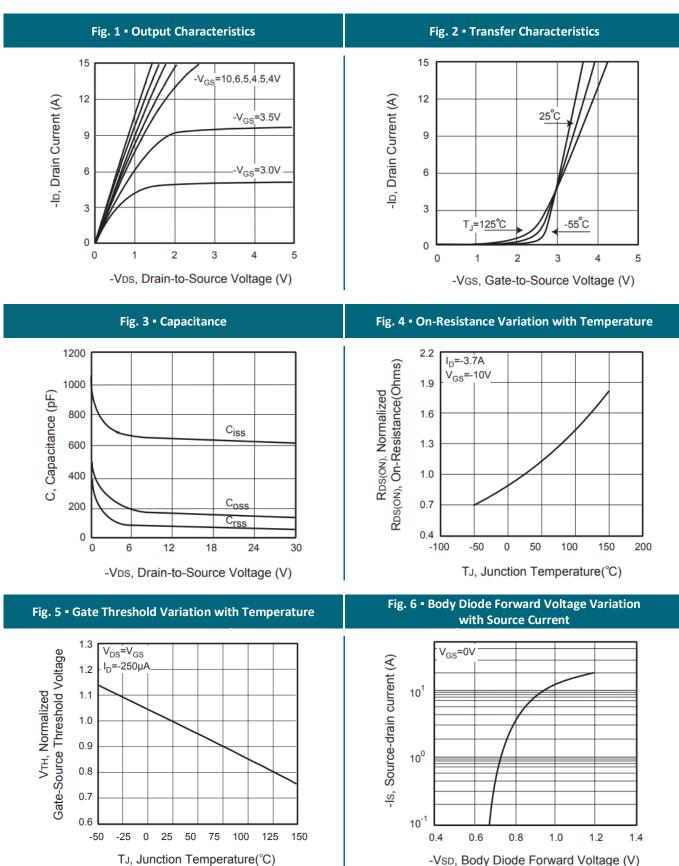


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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

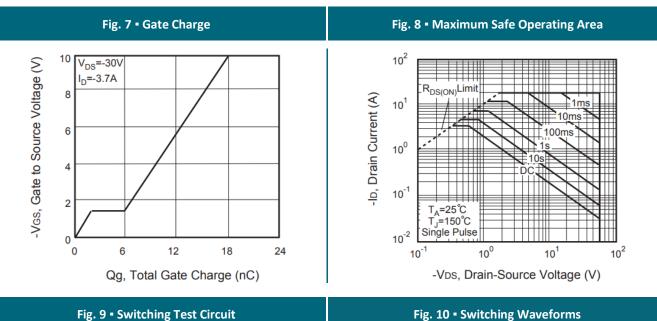
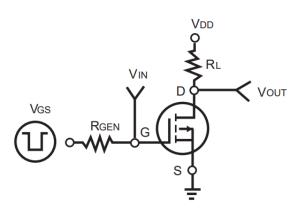
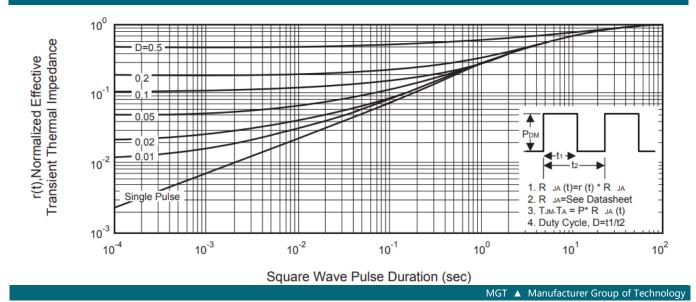


Fig. 9 - Switching Test Circuit



🗲 ton 🗕 toff td(off) tr td(on) tf 90% 90% VOUT INVERTED 0% 10% 90% 50% 50% VIN 10% PULSE WIDTH

Fig. 11 • Normalized Thermal Transient Impedance Curve



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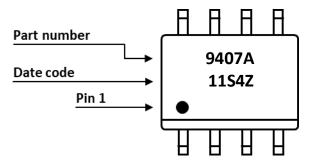
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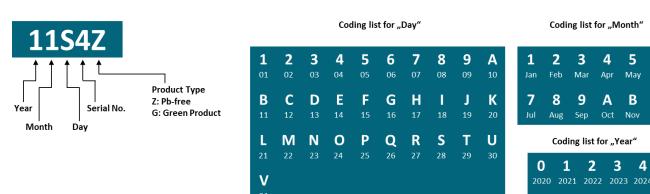
9

PART MARKING



DATE CODE

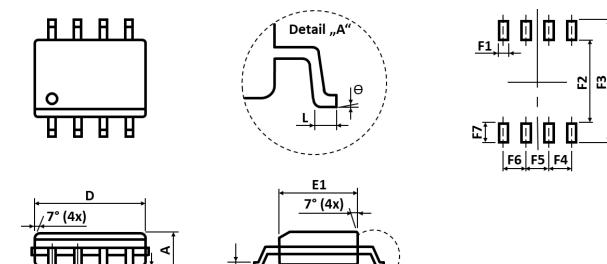
Example: 11S4Z



• Detail "A"



PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	1.350	-	1.750	E1	3.700		4.060
A1	0.100	-	0.250	eB	5.800		6.200
В	0.310	-	0.510	е		1.270	
С	0.170	-	0.250	L	0.400		0.950
D	4.690	-	5.000	θ	0°	-	8°
Sym	Millimeters	Millimeters	Millimeters	Sym	Millimeters	Millimeters	Millimeters

eВ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	-	0.500	-	F5	-	1.270	-	
F2	-	4.250	-	F6	-	1.270	-	
F3	-	6.250	-	F7	-	1.000	-	
F4	-	1.270	-					

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

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ORDERING INFORMATION

В

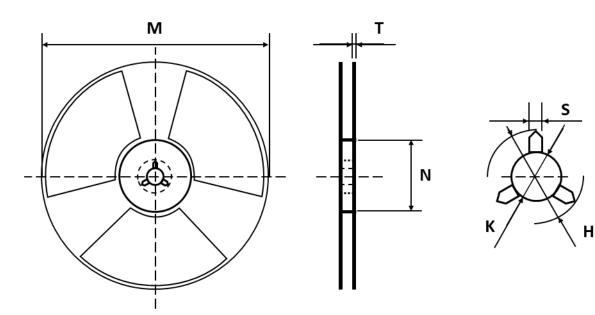
A1

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM9407A	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs



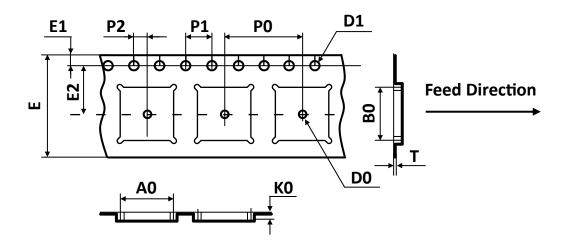


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	Ν	т	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	\$550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

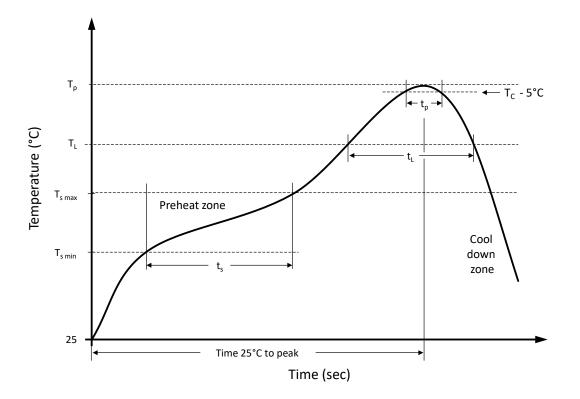
Note: All dimensions meet EIA-481-D requirements.

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RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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